

2SK213, 2SK214, 2SK215, 2SK216

Silicon N-Channel MOS FET

Application

High frequency and low frequency power amplifier,
high speed switching.
Complementary pair with 2SJ76, J77, J78, J79

Features

- Suitable for direct mounting
- High forward transfer admittance
- Excellent frequency response
- Enhancement-mode

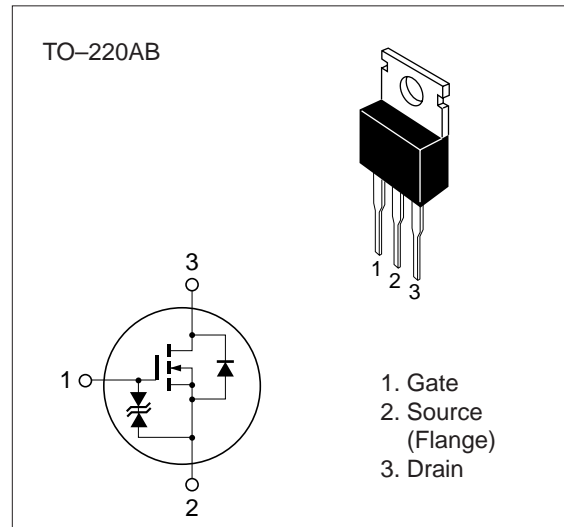


Table 1 Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Item		Symbol	Ratings	Unit
Drain to source voltage	2SK213	V_{DSX}	140	V
	2SK214		160	
	2SK215		180	
	2SK216		200	
Gate to source voltage		V_{GSS}	± 15	V
Drain current		I_D	500	mA
Body to drain diode reverse drain current		I_{DR}	500	mA
Channel dissipation		P_{ch}	1.75	W
		P_{ch}^*	30	W
Channel temperature		T_{ch}	150	$^\circ\text{C}$
Storage temperature		T_{stg}	-45 to +150	$^\circ\text{C}$

* Value at $T_C = 25^\circ\text{C}$

Table 2 Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Item		Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	2SK213	$V_{(BR)DSX}$	140	—	—	V	$I_D = 1 \text{ mA}, V_{GS} = -2 \text{ V}$
	2SK214		160	—	—	V	
	2SK215		180	—	—	V	
	2SK216		200	—	—	V	
Gate to source breakdown voltage		$V_{(BR)GSS}$	± 15	—	—	V	$I_G = \pm 10 \mu\text{A}, V_{DS} = 0$
Gate to source voltage		$V_{GS(on)}$	0.2	—	1.5	V	$I_D = 10 \text{ mA}, V_{DS} = 10 \text{ V}^*$
Drain to source saturation voltage		$V_{DS(sat)}$	—	—	2.0	V	$I_D = 10 \text{ mA}, V_{GD} = 0^*$
Forward transfer admittance		$ y_{fs} $	20	40	—	mS	$I_D = 10 \text{ mA}, V_{DS} = 20 \text{ V}^*$
Input capacitance		C_{iss}	—	90	—	pF	$I_D = 10 \text{ mA}, V_{DS} = 10 \text{ V},$
Reverse transfer capacitance		C_{rss}	—	2.2	—	pF	$f = 1 \text{ MHz}$

* Pulse Test

